

iii HEXFET Power MOSFET (VDSS =-55V, RDS (on) = 0.105 heavy)

Manufacturers	Infineon Technologies Corporation
Package/Case	SOIC-8
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF7342PBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

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Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

Generation V Technology
Ultra Low On-Resistance
Dual P-Channel Mosfet
Surface Mount
Available in Tape & Reel
Dynamic dv/dt Rating
Fast Switching

Features

RoHS Compliant

Low RDS(on)

Dynamic dv/dt Rating

Fast Switching

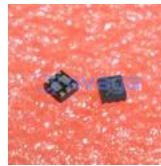
Dual P-Channel MOSFET

Related Products



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Infineon Technologies Corporation
TSOP-6



[IRLHS6376TRPBF](#)

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PQFN2x2DD



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SOIC-8